

YJ Planar Schottky Barrier Diode Die Specification

40V 10A, 84mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB084N040SS-280A

Main Products Characterstics

Maximum Ratings		Static Electrical Characteristics (Ta = 25°C)	
Rating		Parameter	Symbol
		Reverse breakdown voltage	V_{BR}
		$I_F = 10\text{ A}$	
			$\leq 2\%$
		Maximum reverse current	I_R
Maximum ota513(i)-(ing4(ja8((nc2(t)4(N)-6nnt))TETBT1 0 0 1 30.34759.71 Tm30)-e(um)-1per6(a8((cur)2ge))TET EMC 055211 472.03 31.64 23.28 reWh		$V_F = V_{FPM}$	$\leq 2\%$

Device Schematics and Outline Drawing

	Die Thickness *	
	Die Size **	84 Mils
	Top Metal Pad	
	Active Area	
	Top Metal	
	Back Metal	Ag
	Note: 1 *: Also can offer device with 8 mils thickness	
	2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.